

## ADJUSTABLE BATTERY-BACKUP SUPERVISOR FOR RAM RETENTION

### FEATURES

- Supply Current of 40  $\mu$ A (Max)
- Battery Supply Current of 100 nA (Max)
- Supply Voltage Supervision Range:
  - Adjustable
  - Other Versions Available on Request
- Backup-Battery Voltage Can Exceed  $V_{DD}$
- Power-On Reset Generator With Fixed 100-ms Reset Delay Time
- Active-High and Active-Low Reset Output
- Chip-Enable Gating: 3 ns (at  $V_{DD} = 5$  V) Max Propagation Delay
- 10-Pin MSOP Package
- Temperature Range:  $-40^{\circ}\text{C}$  to  $85^{\circ}\text{C}$

### APPLICATIONS

- Fax Machines
- Set-Top Boxes
- Advanced Voice Mail Systems
- Portable Battery-Powered Equipment
- Computer Equipment
- Advanced Modems
- Automotive Systems
- Portable Long-Time Monitoring Equipment
- Point-of-Sale Equipment

### DESCRIPTION

The TPS3613-01 supervisory circuit monitors and controls processor activity by providing backup-battery switchover for data retention of CMOS RAM.

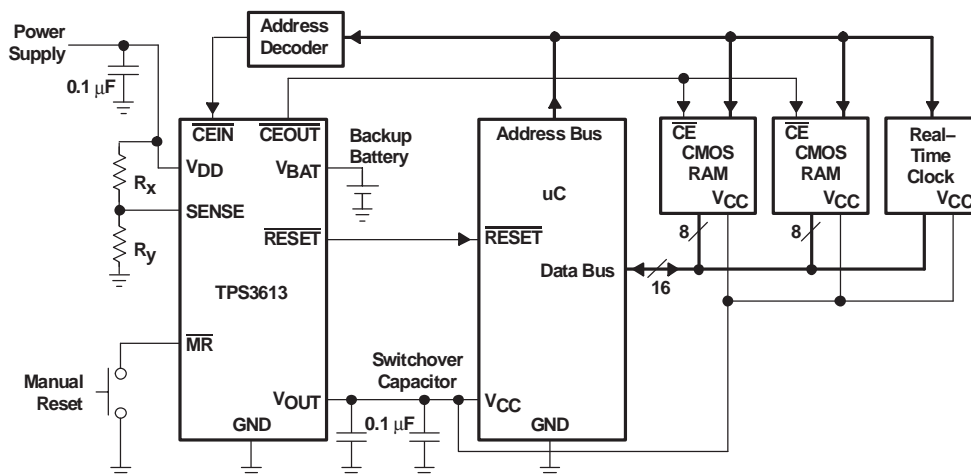
During power-on, reset (RESET and  $\overline{\text{RESET}}$ ) is asserted when the supply voltage ( $V_{DD}$  or  $V_{BAT}$ ) becomes higher than 1.1 V.

Thereafter, the supply voltage supervisor monitors  $V_{DD}$  at the SENSE pin through external feedback resistors and keeps reset active as long as SENSE remains below the threshold voltage,  $V_{IT}$ .

An internal timer delays the release of the reset state to ensure proper system reset. The delay time starts after SENSE rises above the threshold voltage,  $V_{IT}$ .

When SENSE drops below  $V_{IT}$ , reset becomes active again.

The TPS3613-01 is available in a 10-pin MSOP package and is characterized for operation over a temperature range of  $-40^{\circ}\text{C}$  to  $+85^{\circ}\text{C}$ .



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

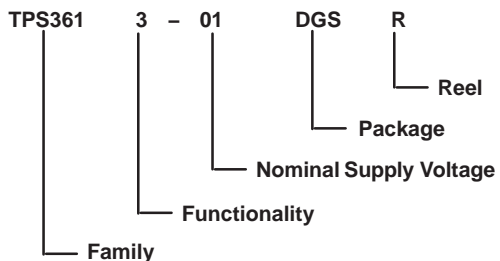
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PACKAGE INFORMATION

T <sub>A</sub>	DEVICE NAME	MARKING
-40°C to +85°C	TPS3613-01DGSR†	AFK

† The DGSR passive indicates tape and reel of 2500 parts.

ordering information application specific versions



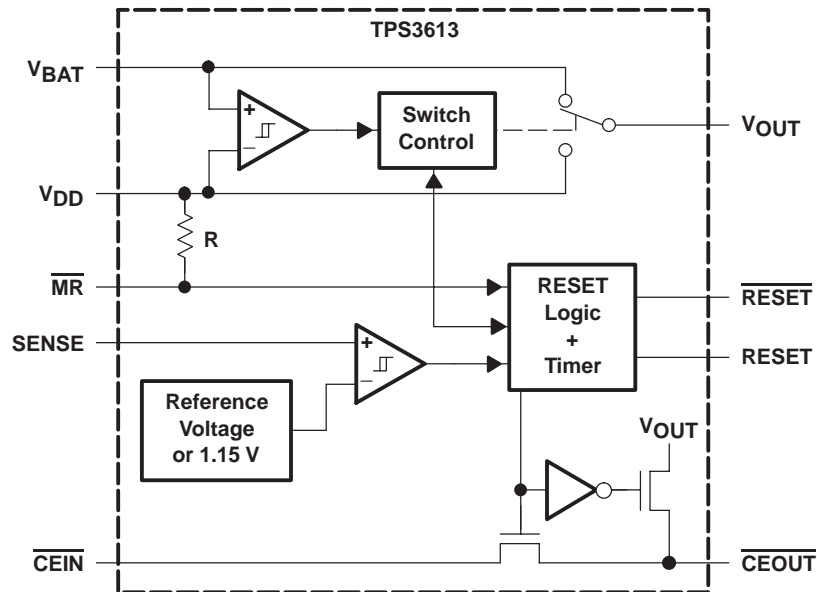
DEVICE NAME	NOMINAL VOLTAGE‡, V <sub>NOM</sub>
TPS3613-01 DGS	Adjustable

‡ For other threshold voltages, contact the local TI sales office for availability and lead-time.

FUNCTION TABLE

SENSE > V <sub>IT</sub>	V <sub>DD</sub> > V <sub>BAT</sub>	$\overline{MR}$	$\overline{CEIN}$	V <sub>OUT</sub>	$\overline{RESET}$	RESET	$\overline{CEOUT}$
0	0	0	0	V <sub>BAT</sub>	0	1	DIS
0	0	0	1	V <sub>BAT</sub>	0	1	DIS
0	0	1	0	V <sub>BAT</sub>	0	1	DIS
0	0	1	1	V <sub>BAT</sub>	0	1	DIS
0	1	0	0	V <sub>DD</sub>	0	1	DIS
0	1	0	1	V <sub>DD</sub>	0	1	DIS
0	1	1	0	V <sub>DD</sub>	0	1	DIS
0	1	1	1	V <sub>DD</sub>	0	1	DIS
1	0	0	0	V <sub>DD</sub>	0	1	DIS
1	0	0	1	V <sub>DD</sub>	0	1	DIS
1	0	1	0	V <sub>DD</sub>	1	0	0
1	0	1	1	V <sub>DD</sub>	1	0	1
1	1	0	0	V <sub>DD</sub>	0	1	DIS
1	1	0	1	V <sub>DD</sub>	0	1	DIS
1	1	1	0	V <sub>DD</sub>	1	0	0
1	1	1	1	V <sub>DD</sub>	1	0	1

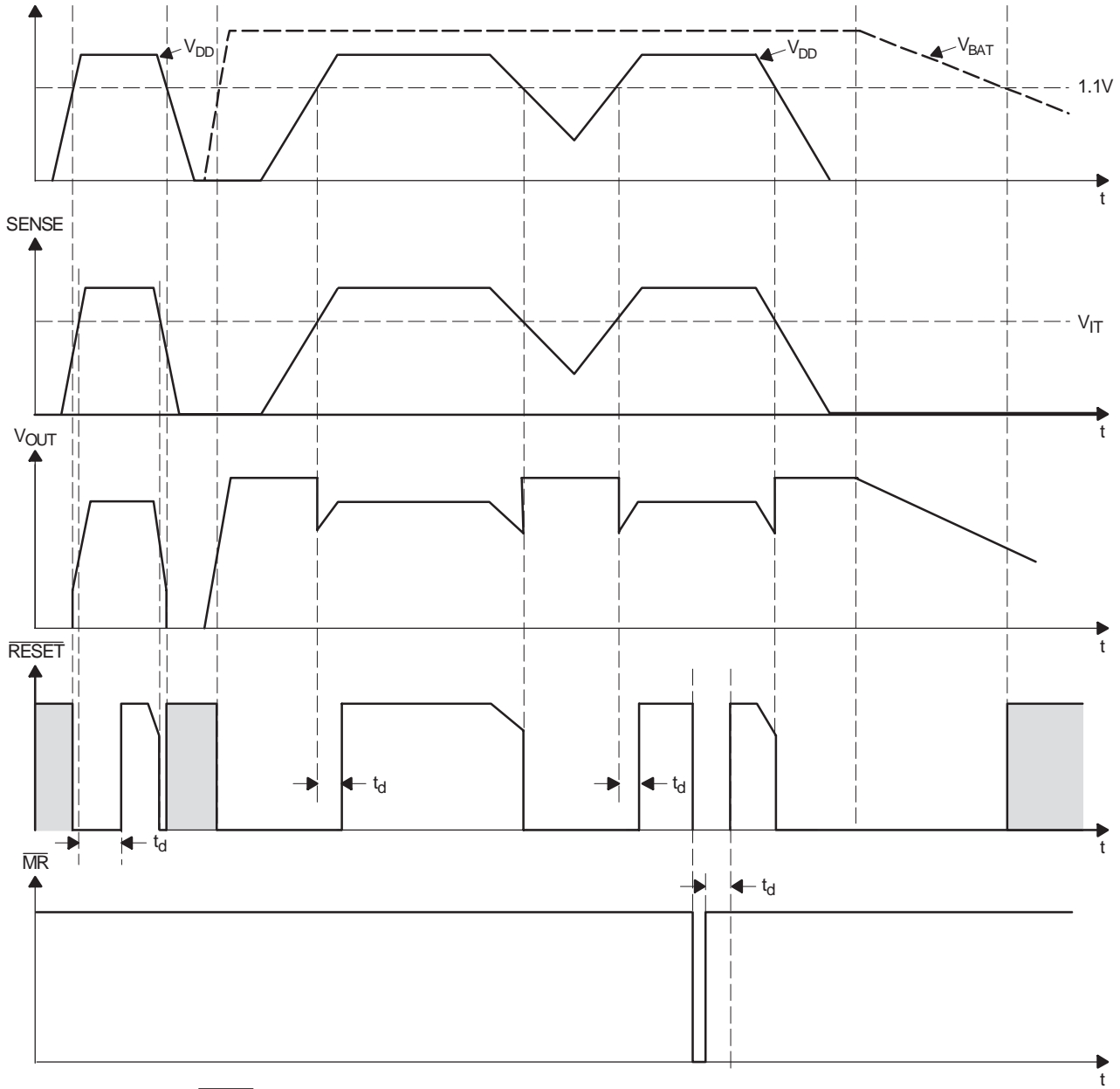
**FUNCTIONAL SCHEMATIC**



**Terminal Functions**

TERMINAL NAME	NO.	I/O	DESCRIPTION
$\overline{\text{CEIN}}$	5	I	Chip-enable input
$\overline{\text{CEOUT}}$	6	O	Chip-enable output
GND	3	I	Ground
$\overline{\text{MR}}$	4	I	Manual reset input
RESET	7	O	Active-high reset output
$\overline{\text{RESET}}$	9	O	Active-low reset output
SENSE	8	I	Adjustable sense input, assumed to be connect to $V_{DD}$ throught feedback resistences. Call your local contacts for other application connections.
$V_{BAT}$	10	I	Backup-battery input
$V_{DD}$	2	I	Input supply voltage
$V_{OUT}$	1	O	Supply output

**TIMING DIAGRAM**



NOTE: Shaded area in  $\overline{\text{RESET}}$  is *undefined*.

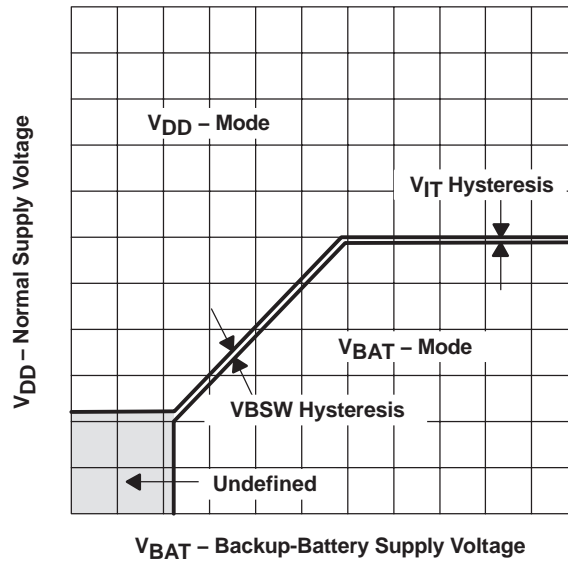
**detailed description**

**backup-battery switchover**

In case of a brownout or power failure, it may be necessary to preserve the contents of RAM. If a backup battery is installed at  $V_{BAT}$ , the device automatically switches the connected RAM to backup power when  $V_{DD}$  fails. In order to allow the backup battery (for example, 3.6-V lithium cells) to have a higher voltage than  $V_{DD}$ , these

supervisors do not connect  $V_{BAT}$  to  $V_{OUT}$  when  $V_{BAT}$  is greater than  $V_{DD}$ .  $V_{BAT}$  only connects to  $V_{OUT}$  (through a 15- $\Omega$  switch) when  $V_{DD}$  falls below  $V_{IT}$  and  $V_{BAT}$  is greater than  $V_{DD}$ . When  $V_{DD}$  recovers, switchover is deferred either until  $V_{DD}$  crosses  $V_{BAT}$ , or when  $V_{DD}$  rises above the reset threshold  $V_{IT}$ .  $V_{OUT}$  connects to  $V_{DD}$  through a 1- $\Omega$  (max) PMOS switch when  $V_{DD}$  crosses the reset threshold.

$V_{DD} > V_{BAT}$	$V_{DD} > V_{IT}$	$V_{OUT}$
1	1	$V_{DD}$
1	0	$V_{DD}$
0	1	$V_{DD}$
0	0	$V_{BAT}$



**Figure 1.  $V_{DD}$  -  $V_{BAT}$  Switchover**

**detailed description (continued)**

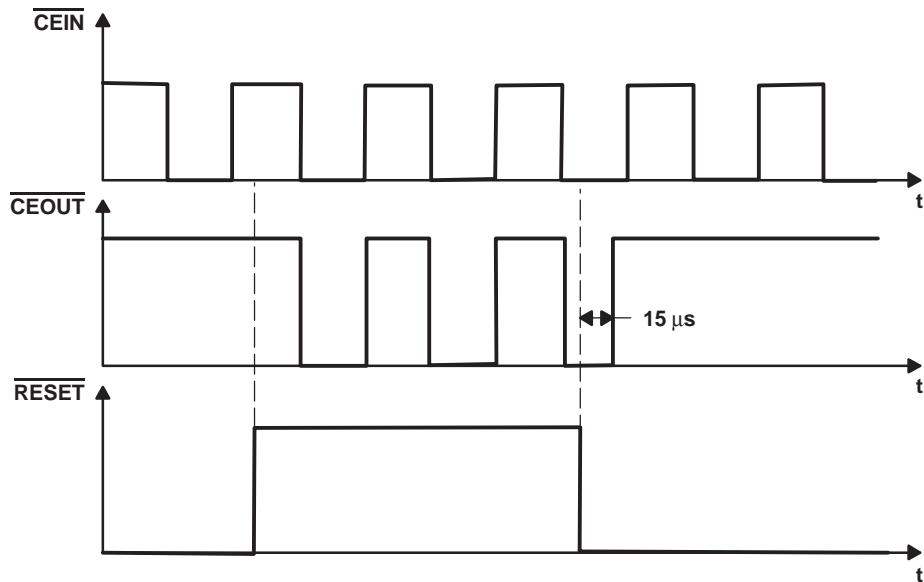
**chip-enable signal gating**

The internal gating of chip-enable ( $\overline{CE}$ ) signals prevents erroneous data from corrupting CMOS RAM during an under-voltage condition. The TPS3613 uses a series transmission gate from  $\overline{CEIN}$  to  $\overline{CEOUT}$ . During normal operation (reset not asserted), the CE transmission gate is enabled and passes all CE transitions. When reset is asserted, this path becomes disabled, preventing erroneous data from corrupting the CMOS RAM. The short CE propagation delay from  $\overline{CEIN}$  to  $\overline{CEOUT}$  enables the TPS3613 device to be used with most processors.

The CE transmission gate is disabled and  $\overline{CEIN}$  is in high impedance (disable mode) while reset is asserted. During a power-down sequence when  $V_{DD}$  crosses the reset threshold, the CE transmission gate is disabled and  $\overline{CEIN}$  immediately becomes high impedance if the voltage at  $\overline{CEIN}$  is high. If  $\overline{CEIN}$  is low when reset

is asserted, the CE transmission gate is disabled when  $\overline{CEIN}$  goes high, or 15  $\mu s$  after reset asserts, whichever occurs first. This allows the current write cycle to complete during power down. When the CE transmission gate is enabled, the impedance of  $\overline{CEIN}$  appears as a resistor in series with the load at  $\overline{CEOUT}$ . The overall device propagation delay through the CE transmission gate depends on  $V_{OUT}$ , the source impedance of the drive connected to  $\overline{CEIN}$ , and the load at  $\overline{CEOUT}$ . To achieve minimum propagation delay, the capacitive load at  $\overline{CEOUT}$  should be minimized, and a low-output-impedance driver is used.

In the disabled mode, the transmission gate is off and an active pullup connects  $\overline{CEOUT}$  to  $V_{OUT}$ . This pullup turns off when the transmission gate is enabled.



**Figure 2. Chip-Enable Timing**

**ABSOLUTE MAXIMUM RATINGS**

**OVER OPERATING FREE-AIR TEMPERATURE (unless otherwise noted)<sup>(1)</sup>**

Supply voltage: $V_{DD}$ <sup>(2)</sup> .....	7 V
MR and SENSE pins <sup>(2)</sup> .....	-0.3 V to ( $V_{DD} + 0.3$ V)
Continuous output current at $V_{OUT}$ : $I_O$ .....	400 mA
All other pins, $I_O$ .....	±10 mA
Continuous total power dissipation .....	See Dissipation Rating Table
Operating free-air temperature range, $T_A$ .....	-40°C to +85°C
Storage temperature range, $T_{stg}$ .....	-65°C to +150°C
Lead temperature soldering 1,6 mm (1/16 inch) from case for 10 seconds .....	+260°C

(1) Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltage values are with respect to GND. For reliable operation the device must not operate at 7 V for more than  $t = 1000$ h continuously.

**DISSIPATION RATING TABLE**

PACKAGE	$T_A \leq +25^\circ\text{C}$ POWER RATING	DERATING FACTOR ABOVE $T_A = +25^\circ\text{C}$	$T_A = +70^\circ\text{C}$ POWER RATING	$T_A = +85^\circ\text{C}$ POWER RATING
DGS	424 mW	3.4 mW/°C	271 mW	220 mW

**RECOMMENDED OPERATING CONDITIONS**

	MIN	MAX	UNIT
Supply voltage, $V_{DD}$	1.65	5.5	V
Battery supply voltage, $V_{BAT}$	1.5	5.5	V
Input voltage, $V_I$	0	$V_{DD} + 0.3$	V
High-level input voltage, $V_{IH}$	$0.7 \times V_{DD}$		V
Low-level input voltage, $V_{IL}$	$0.3 \times V_{DD}$		V
Continuous output current at $V_{OUT}$ , $I_O$	300		mA
Input transition rise and fall rate at MR, $\Delta t/\Delta V$	100		ns/V
Slew rate at $V_{DD}$ or $V_{bat}$	1		V/ $\mu$ s
Operating free-air temperature range, $T_A$	-40	+85	°C

**ELECTRICAL CHARACTERISTICS  
OVER RECOMMENDED OPERATING CONDITIONS (unless otherwise noted)**

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT	
V <sub>OH</sub>	High-level output voltage	$\overline{\text{RESET}}$	V <sub>DD</sub> = 1.8 V, I <sub>OH</sub> = -400 μA	V <sub>DD</sub> - 0.2 V		V	
			V <sub>DD</sub> = 3.3 V, I <sub>OH</sub> = -2 mA V <sub>DD</sub> = 5 V, I <sub>OH</sub> = -3 mA	V <sub>DD</sub> - 0.4 V			
		$\overline{\text{RESET}}$	V <sub>DD</sub> = 1.8 V, I <sub>OH</sub> = -20 μA	V <sub>DD</sub> - 0.3 V			
			V <sub>DD</sub> = 3.3 V, I <sub>OH</sub> = -80 μA V <sub>DD</sub> = 5 V, I <sub>OH</sub> = -120 μA	V <sub>DD</sub> - 0.4 V			
		$\overline{\text{CEOUT}}$	V <sub>OUT</sub> = 1.8 V, I <sub>OH</sub> = -1 mA	V <sub>OUT</sub> - 0.2 V			
		Enable mode CEIN = V <sub>OUT</sub>	V <sub>OUT</sub> = 3.3 V, I <sub>OH</sub> = -2 mA V <sub>OUT</sub> = 5 V, I <sub>OH</sub> = -5 mA	V <sub>OUT</sub> - 0.3 V			
$\overline{\text{CEOUT}}$ Disable mode	V <sub>OUT</sub> = 3.3 V, I <sub>OH</sub> = -0.5 mA	V <sub>OUT</sub> - 0.4 V					
V <sub>OL</sub>	Low-level output voltage	$\overline{\text{RESET}}$	V <sub>DD</sub> = 1.8 V, I <sub>OL</sub> = 400 μA	0.2		V	
		$\overline{\text{RESET}}$	V <sub>DD</sub> = 3.3 V, I <sub>OL</sub> = 2 mA V <sub>DD</sub> = 5 V, I <sub>OL</sub> = 3 mA	0.4			
		$\overline{\text{CEOUT}}$	V <sub>OUT</sub> = 1.8 V, I <sub>OL</sub> = 1.0 mA	0.2			
		Enable mode CEIN = 0 V	V <sub>OUT</sub> = 3.3 V, I <sub>OL</sub> = 2 mA V <sub>OUT</sub> = 5 V, I <sub>OL</sub> = 5 mA	0.3			
		Power-up reset voltage (see Note 1)	V <sub>DD</sub> > 1.1 V or V <sub>BAT</sub> > 1.1 V, I <sub>OL</sub> = 20 μA	0.4		V	
V <sub>OUT</sub>	Normal mode	I <sub>O</sub> = 8.5 mA, V <sub>DD</sub> = 1.8 V, V <sub>BAT</sub> = 0 V	V <sub>DD</sub> - 50 mV		V		
		I <sub>O</sub> = 125 mA, V <sub>DD</sub> = 3.3 V, V <sub>BAT</sub> = 0 V	V <sub>DD</sub> - 150 mV				
		I <sub>O</sub> = 200 mA, V <sub>DD</sub> = 5 V, V <sub>BAT</sub> = 0 V	V <sub>DD</sub> - 200 mV				
	Battery-backup mode	I <sub>O</sub> = 0.5 mA, V <sub>BAT</sub> = 1.5 V, V <sub>DD</sub> = 0 V	V <sub>BAT</sub> - 20 mV				
		I <sub>O</sub> = 7.5 mA, V <sub>BAT</sub> = 3.3 V, V <sub>DD</sub> = 0 V	V <sub>BAT</sub> - 113 mV				
R <sub>DSON</sub>	V <sub>DD</sub> to V <sub>OUT</sub> on-resistance	V <sub>DD</sub> = 5 V	0.6	1	Ω		
	V <sub>BAT</sub> to V <sub>OUT</sub> on-resistance	V <sub>BAT</sub> = 3.3 V	8	15			
V <sub>IT</sub>	Negative-going input threshold voltage (see Note 2)		1.13	1.15	1.17	V	
V <sub>hys</sub>	Hysteresis	Sense	1.1 V < V <sub>IT</sub> < 1.65 V		12	mV	
		V <sub>BSW</sub> (see Note 3)	V <sub>DD</sub> = 1.8 V		55		
I <sub>IH</sub>	High-level input current	$\overline{\text{MR}}$	MR = 0.7 x V <sub>DD</sub> , V <sub>DD</sub> = 5 V		-33	μA	
I <sub>IL</sub>	Low-level input current	$\overline{\text{MR}}$	MR = 0 V, V <sub>DD</sub> = 5 V		-110		
I <sub>I</sub>	Input current	SENSE	V <sub>DD</sub> = 1.15 V		-25	25	nA
I <sub>DD</sub>	V <sub>DD</sub> supply current		V <sub>OUT</sub> = V <sub>DD</sub>		40	μA	
			V <sub>OUT</sub> = V <sub>BAT</sub>		40		
I <sub>BAT</sub>	V <sub>BAT</sub> supply current		V <sub>OUT</sub> = V <sub>DD</sub>		-0.1	0.1	μA
			V <sub>OUT</sub> = V <sub>BAT</sub>			0.5	
I <sub>Ikg</sub>	$\overline{\text{CEIN}}$ leakage current	Disable mode, V <sub>I</sub> < V <sub>DD</sub>			±1		μA
C <sub>i</sub>	Input capacitance	V <sub>I</sub> = 0 V to 5 V			5	pF	

(1) The lowest voltage at which  $\overline{\text{RESET}}$  becomes active.  $t_r(V_{DD}) \geq 15 \mu\text{s/V}$ .

(2) To ensure best stability of the threshold voltage, a bypass capacitor (ceramic, 0.1 μF) should be placed near to the supply terminals.

(3) For V<sub>DD</sub> < 1.6 V, V<sub>OUT</sub> switches to V<sub>BAT</sub> regardless of V<sub>BAT</sub>



**TIMING REQUIREMENTS AT  $R_L = 1\text{ M}\Omega$ ,  $C_L = 50\text{ PF}$ ,  $T_A = -40^\circ\text{C TO } +85^\circ\text{C}$** 

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$t_w$	Pulse width	SENSE	$V_{IH} = V_{IT} + 0.2\text{ V}$ , $V_{IL} = V_{IT} - 0.2\text{ V}$	6		$\mu\text{s}$

**SWITCHING CHARACTERISTICS AT  $R_L = 1\text{ M}\Omega$ ,  $C_L = 50\text{ PF}$ ,  $T_A = -40^\circ\text{C TO } +85^\circ\text{C}$** 

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT	
$t_d$	Delay time	$V_{SENSE} \geq V_{IT} + 0.2\text{ V}$ , $MR \geq 0.7 \times V_{DD}$ , See timing diagram	60	100	140	ms	
$t_{PLH}$	Propagation (delay) time, low-to-high-level output	50% $\overline{\text{RESET}}$ to 50% $\overline{\text{CEOUT}}$		15		$\mu\text{s}$	
$t_{PHL}$	Propagation (delay) time, high-to-low-level output	$V_{DD} = 1.8\text{ V}$		5	15	ns	
		$V_{DD} = 3.3\text{ V}$		1.6	5		
		$V_{DD} = 5\text{ V}$		1	3		
		SENSE to $\overline{\text{RESET}}$	$V_{IL} = V_{IT} - 0.2\text{ V}$ , $V_{IH} = V_{IT} + 0.2\text{ V}$		2	5	$\mu\text{s}$
		$\overline{\text{MR}}$ to $\overline{\text{RESET}}$	$V_{SENSE} \geq V_{IT} + 0.2\text{ V}$ , $V_{IL} = 0.3 \times V_{DD}$ , $V_{IH} = 0.7 \times V_{DD}$		0.1	1	$\mu\text{s}$
	Transition time	$V_{DD}$ to $V_{BAT}$	$V_{IH} = V_{BAT} + 0.2\text{ V}$ , $V_{IL} = V_{BAT} - 0.2\text{ V}$ , $V_{BAT} < V_{IT}$			3	$\mu\text{s}$

(1) Assured by design

TYPICAL CHARACTERISTICS

Table of Graphs

			FIGURE
$r_{DS(on)}$	Static drain-source on-state resistance ( $V_{DD}$ to $V_{OUT}$ )	vs Output current	3
	Static drain-source on-state resistance ( $V_{BAT}$ to $V_{OUT}$ )	vs Output current	4
	Static drain-source on-state resistance ( $CEIN$ to $CEOUT$ )	vs Input voltage at $CEIN$	5
$I_{DD}$	Supply current	vs Supply voltage	6
$V_{IT}$	Input threshold voltage at $\overline{RESET}$	vs Free-air temperature	7
$V_{OH}$	High-level output voltage at $\overline{RESET}$	vs High-level output current	8, 9
	High-level output voltage at $\overline{CEOUT}$		10, 11, 12, 13
$V_{OL}$	Low-level output voltage at $\overline{RESET}$	vs Low-level output current	14, 15
	Low-level output voltage at $\overline{CEOUT}$	vs Low-level output current	16, 17

STATIC DRAIN-SOURCE ON-STATE RESISTANCE ( $V_{DD}$  to  $V_{OUT}$ ) vs OUTPUT CURRENT

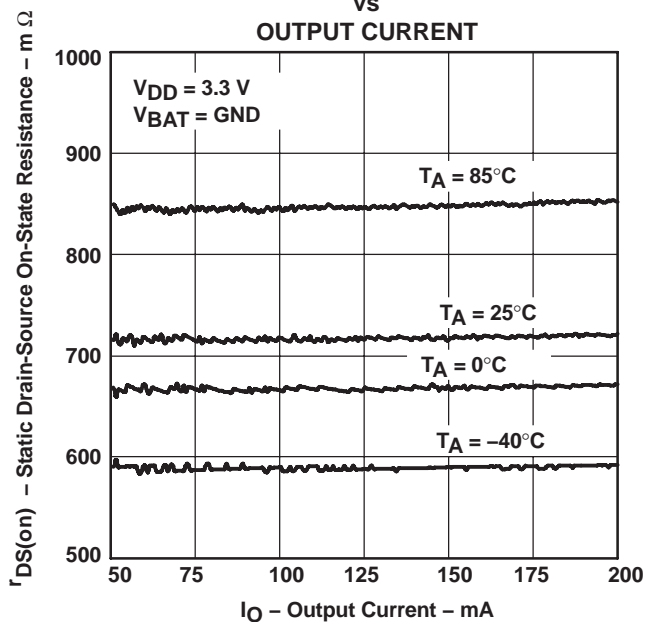


Figure 3

STATIC DRAIN-SOURCE ON-STATE RESISTANCE ( $V_{BAT}$  to  $V_{OUT}$ ) vs OUTPUT CURRENT

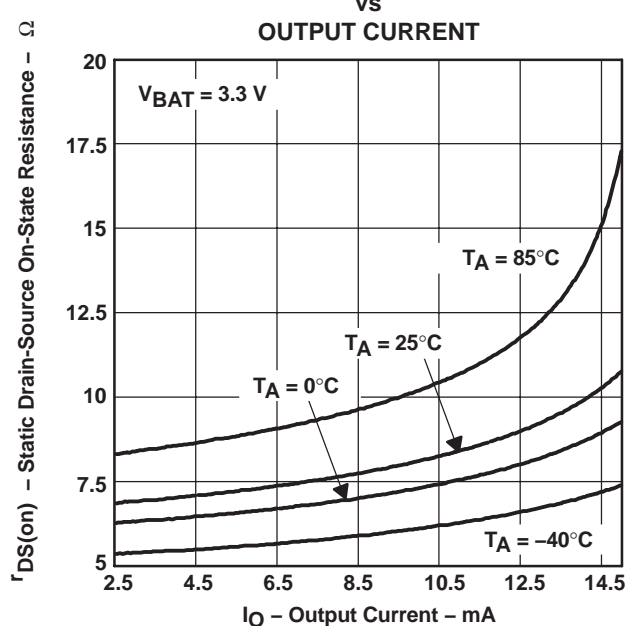


Figure 4

TYPICAL CHARACTERISTICS

STATIC DRAIN-SOURCE ON-STATE RESISTANCE  
( $\overline{CEIN}$  to  $\overline{CEOUT}$ )

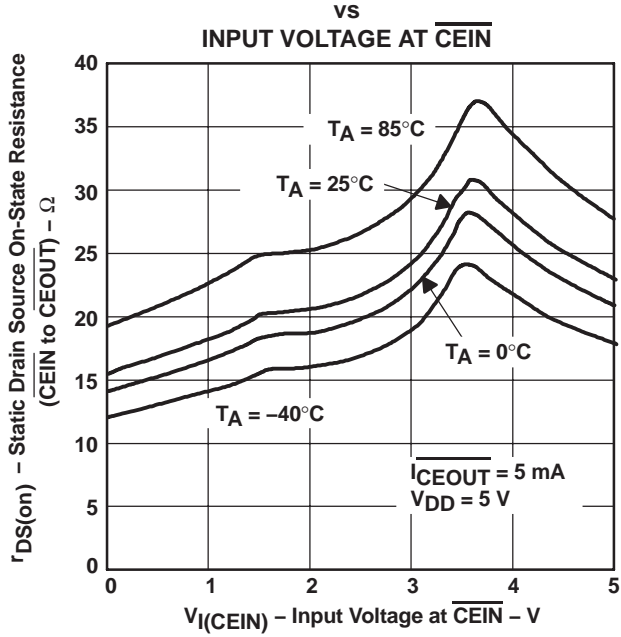


Figure 5

SUPPLY CURRENT  
vs  
SUPPLY VOLTAGE

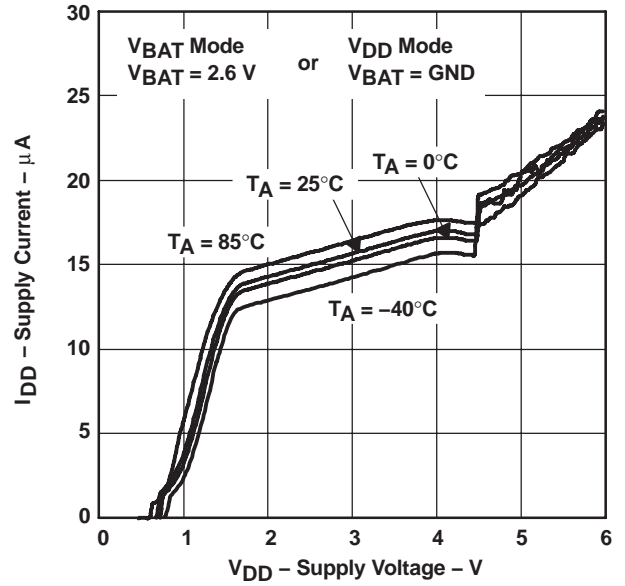


Figure 6

INPUT THRESHOLD VOLTAGE AT  $\overline{RESET}$   
vs  
FREE-AIR TEMPERATURE

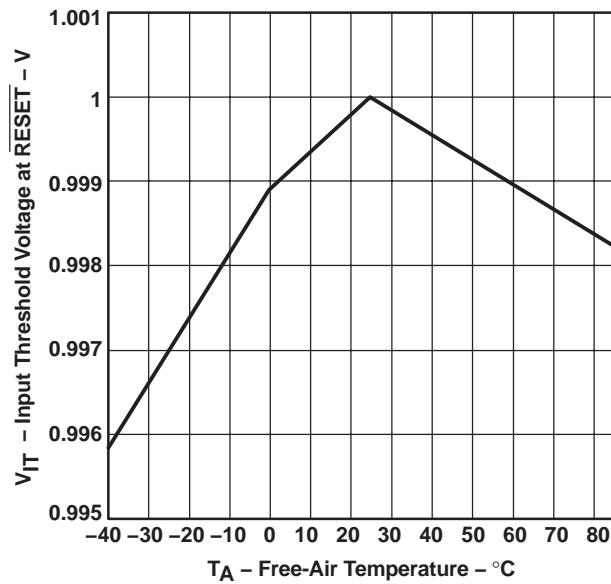


Figure 7

TYPICAL CHARACTERISTICS

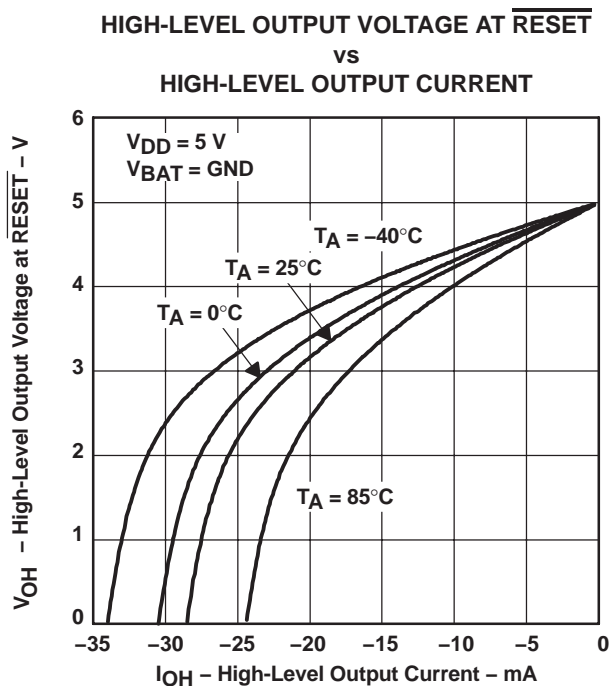


Figure 8

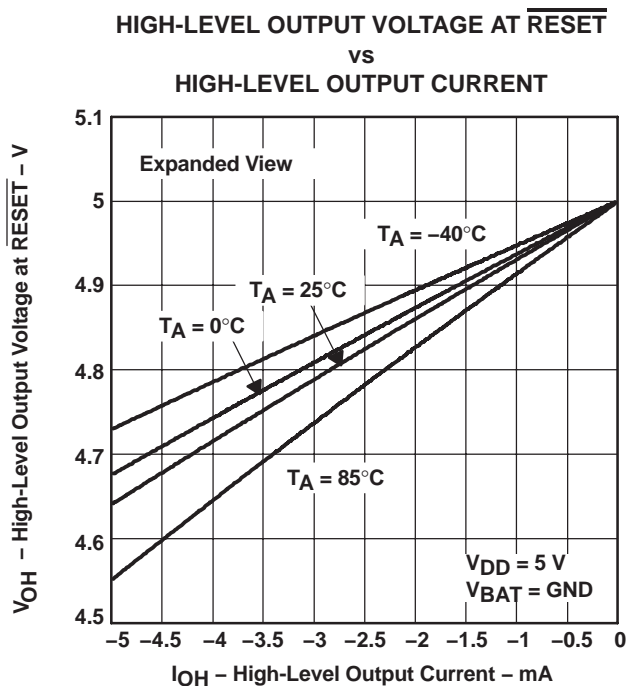


Figure 9

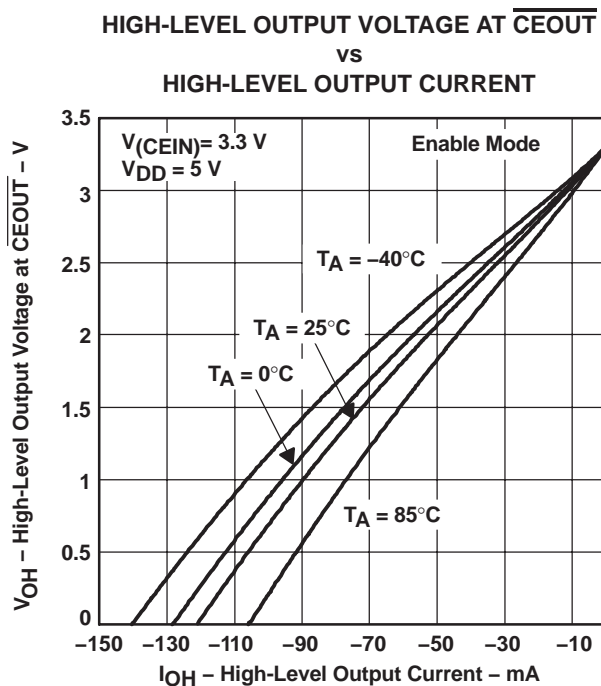


Figure 10

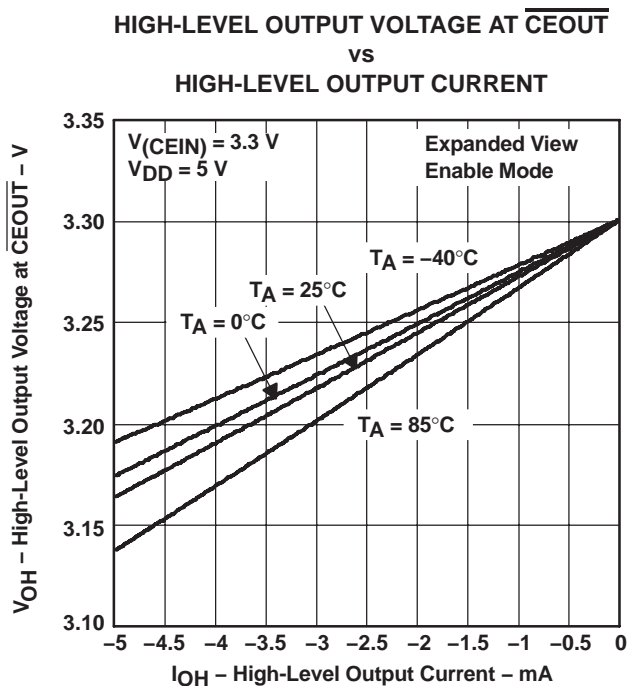
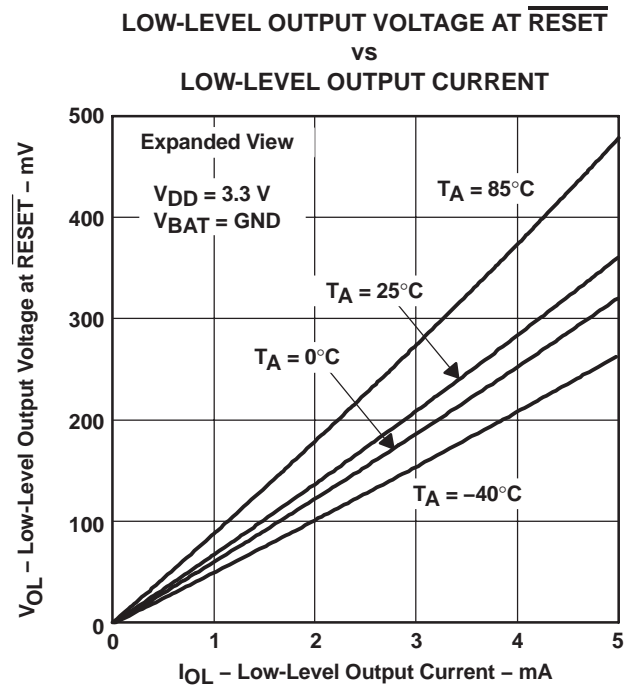
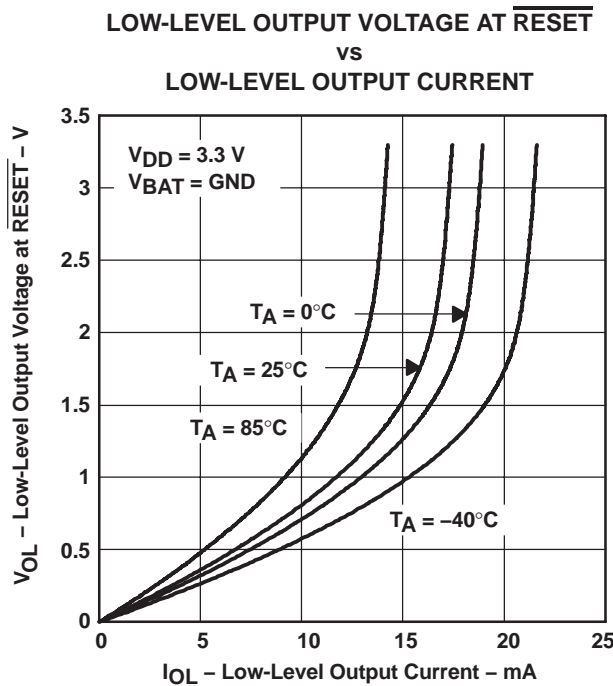
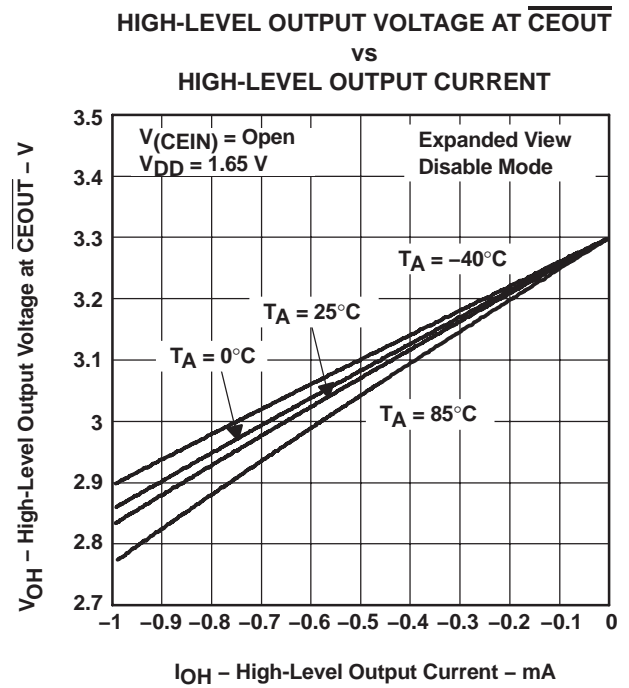
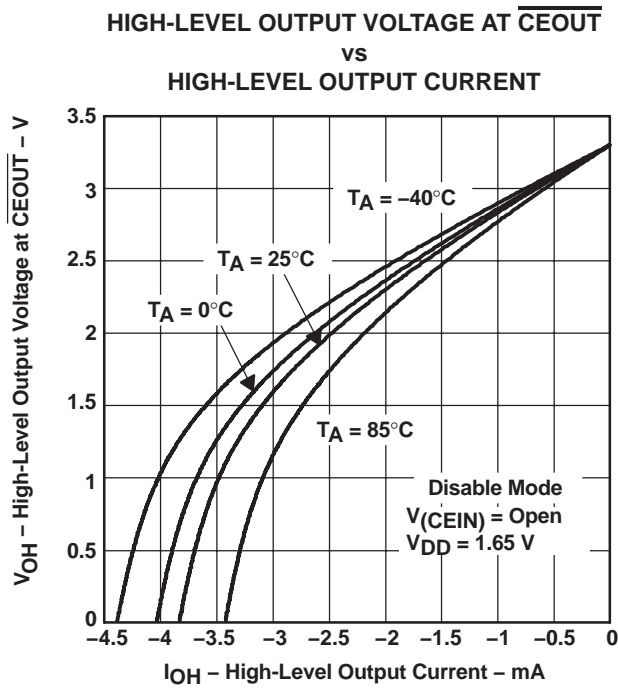


Figure 11

TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS

LOW-LEVEL OUTPUT VOLTAGE AT  $\overline{CEOUT}$   
vs  
LOW-LEVEL OUTPUT CURRENT

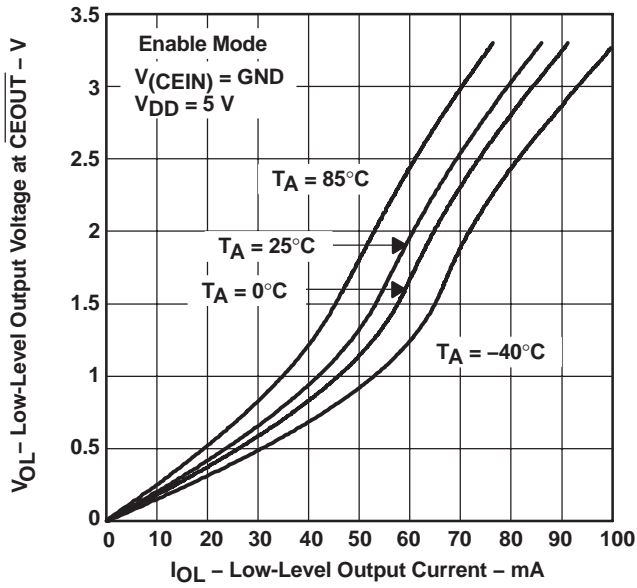


Figure 16

LOW-LEVEL OUTPUT VOLTAGE AT  $\overline{CEOUT}$   
vs  
LOW-LEVEL OUTPUT CURRENT

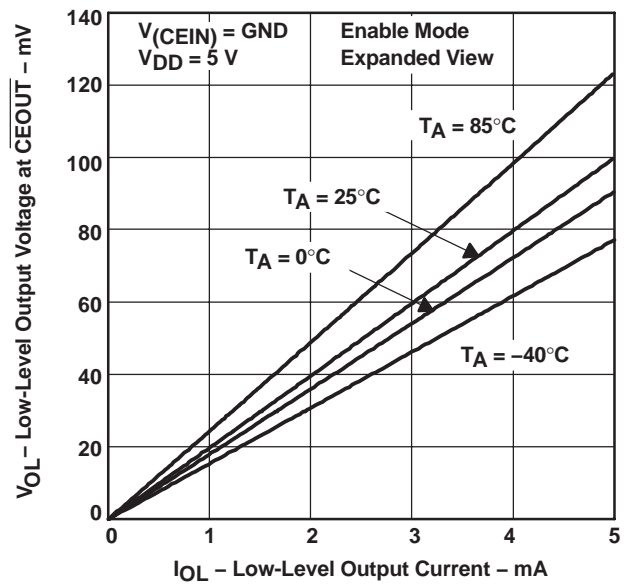


Figure 17

**PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TPS3613-01DGS	ACTIVE	VSSOP	DGS	10	80	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	AFK	<a href="#">Samples</a>
TPS3613-01DGSR	ACTIVE	VSSOP	DGS	10	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	AFK	<a href="#">Samples</a>

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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## TAPE AND REEL INFORMATION



### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS3613-01DGSR	VSSOP	DGS	10	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1

**TAPE AND REEL BOX DIMENSIONS**



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS3613-01DGSR	VSSOP	DGS	10	2500	358.0	335.0	35.0

# DGS0010A



# PACKAGE OUTLINE

## VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



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### NOTES:

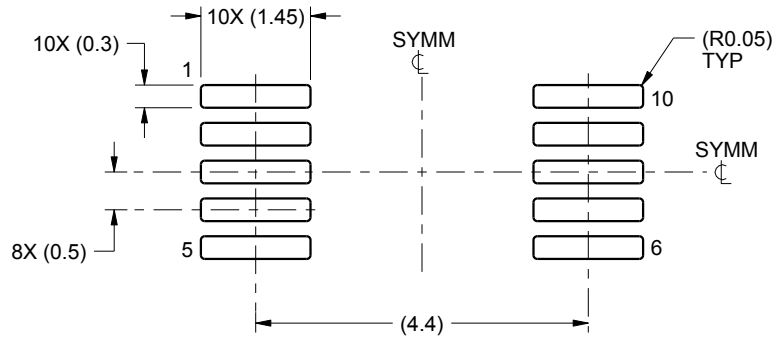
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-187, variation BA.

# EXAMPLE BOARD LAYOUT

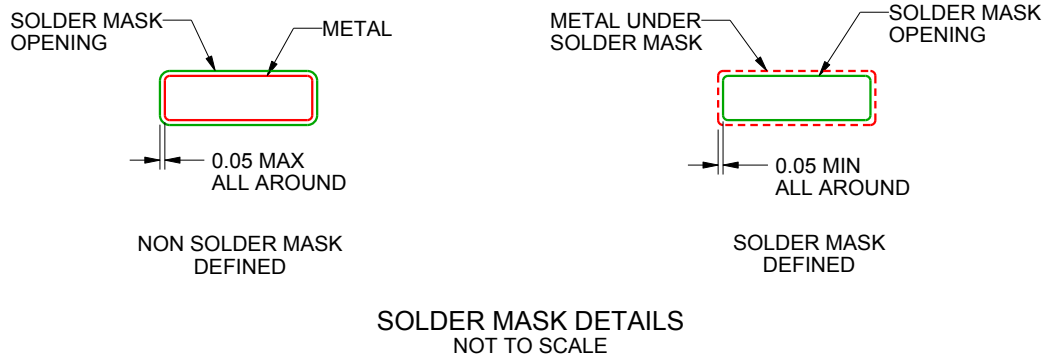
DGS0010A

VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE  
SCALE:10X



SOLDER MASK DETAILS  
NOT TO SCALE

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NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

# EXAMPLE STENCIL DESIGN

DGS0010A

VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE  
BASED ON 0.125 mm THICK STENCIL  
SCALE:10X

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NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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